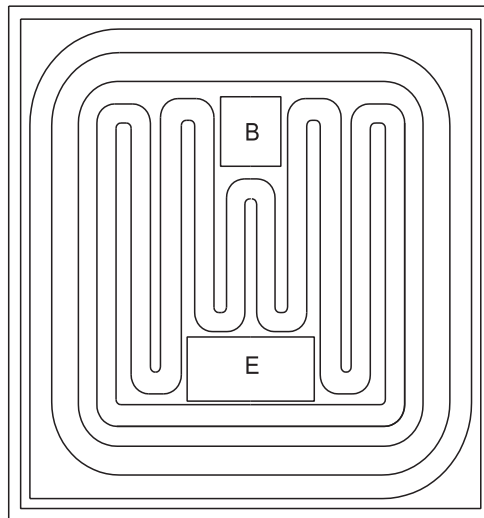


# PRELIMINARY

## PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	30 x 30 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.85 x 4.20 MILS
Emitter Bonding Pad Area	7.35 x 3.75 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 15,000Å

## GEOMETRY



BACKSIDE COLLECTOR

## GROSS DIE PER 4 INCH WAFER

12,300

## PRINCIPAL DEVICE TYPES

2N3467

2N3468

R0

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